

### **INCHANGE SEMICONDUCTOR**

# isc N-Channel MOSFET Transistor

### FDP047N10

#### FEATURES With TO-220 packaging D(2) · Drain Source Voltage-: V<sub>DSS</sub> ≥ 100V Static drain-source on-resistance: $R_{DS}(on) \le 4.7 m \Omega @V_{GS} = 10V$ 100% avalanche tested 5/3 Minimum Lot-to-Lot variations for robust device pin 1.Gate performance and reliable operation 2.Drain 123 3. Source TO-220 package APPLICATIONS · Power supply Switching applications -S ABSOLUTE MAXIMUM RATINGS(Ta=25°C) SYMBOL PARAMETER VALUE UNIT 100 **Drain-Source Voltage** V VDSS Gate-Source Voltage ±20 V<sub>GSS</sub> V Drain Current-Continuous;@Tc=25°C 164 $I_D$ А C **I**DM Drain Current-Single Pulsed 656 А mm $\mathbf{P}_{\mathsf{D}}$ Total Dissipation 375 W DIM MIN MAX 15.50 15.90 A 10.20 °C 9.80 Ti **Operating Junction Temperature** -55~175 В 4.20 C 4.50 D 0.70 0.90 Storage Temperature -55~175 °C Tstg F 3.40 4.98 G Н 2.68 2.900.44 0.60 THERMAL CHARACTERISTICS Κ 2.80 13.401.20 .45

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.4	°C/W

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2.70

2.30

1.29

6.45

8.66

2.90

2.70

1.35

6.65

8.86

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#### **ELECTRICAL CHARACTERISTICS**

#### $T_{\rm C}\text{=}25^\circ\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 250uA	100			V
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =250uA	2.5		4.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 75A			4.7	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V;V <sub>DS</sub> = 0V			±100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 100V; V <sub>GS</sub> = 0V V <sub>DS</sub> = 100V; V <sub>GS</sub> = 0V;T <sub>J</sub> =150°C			1 500	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> = 75A, V <sub>GS</sub> = 0 V			1.25	V

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